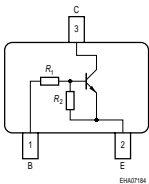
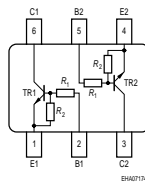


NPN Silicon Digital Transistor

- Switching circuit, inverter, interface circuit driver circuit
- Built in bias resistor ($R_1=47\text{ k}\Omega$, $R_2=47\text{ k}\Omega$)
- BCR148S: Two internally isolated transistors with good matching in one multichip package
- BCR148S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101


**BCR148
BCR148W**

BCR148S


Type	Marking	Pin Configuration						Package
		1=B	2=E	3=C	-	-	-	
BCR148	WEs	1=B	2=E	3=C	-	-	-	SOT23
BCR148S	WEs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BCR148W	WEs	1=B	2=E	3=C	-	-	-	SOT323

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	80	
Input reverse voltage	$V_{i(rev)}$	10	
Collector current	I_C	100	mA
Total power dissipation- BCR148, $T_S \leq 102^\circ\text{C}$ BCR148S, $T_S \leq 115^\circ\text{C}$ BCR148W, $T_S \leq 124^\circ\text{C}$	P_{tot}	200 250 250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 240 ≤ 140 ≤ 105	K/W
BCR148			
BCR148S			
BCR148W			

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

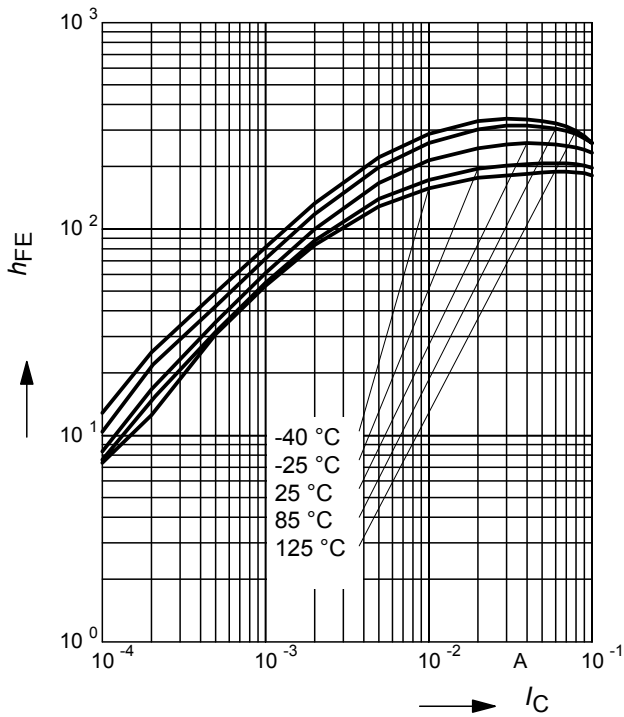
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 10 \text{ V}, I_C = 0$	I_{EBO}	-	-	164	μA
DC current gain ¹⁾ $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	h_{FE}	70	-	-	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(off)}$	0.8	-	1.5	
Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0.3 \text{ V}$	$V_{i(on)}$	1	-	3	
Input resistor	R_1	32	47	62	$\text{k}\Omega$
Resistor ratio	R_1/R_2	0.9	1	1.1	-
AC Characteristics					
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	f_T	-	100	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{cb}	-	3	-	pF

¹Pulse test: $t < 300 \mu\text{s}$; $D < 2\%$

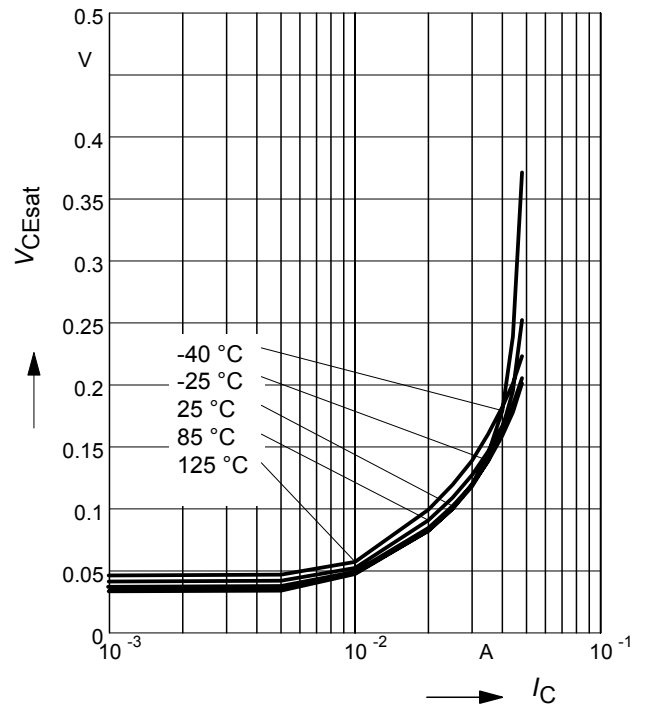
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



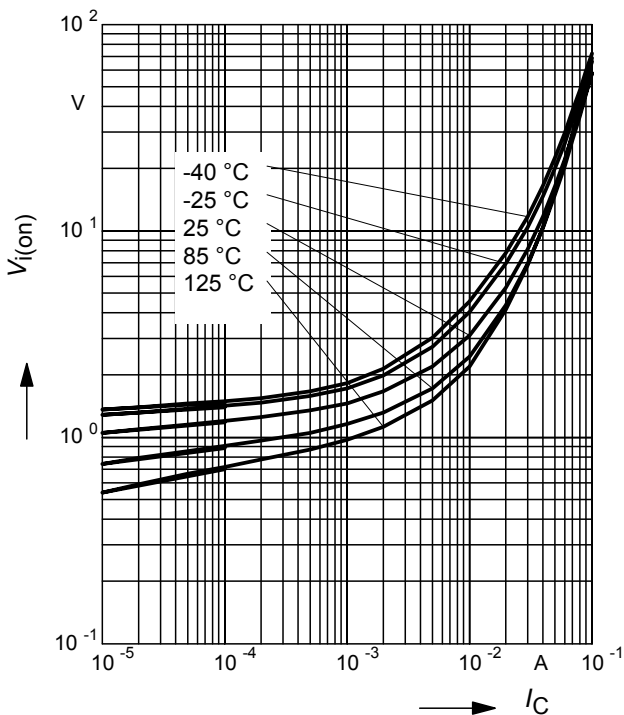
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C), I_C/I_B = 20$



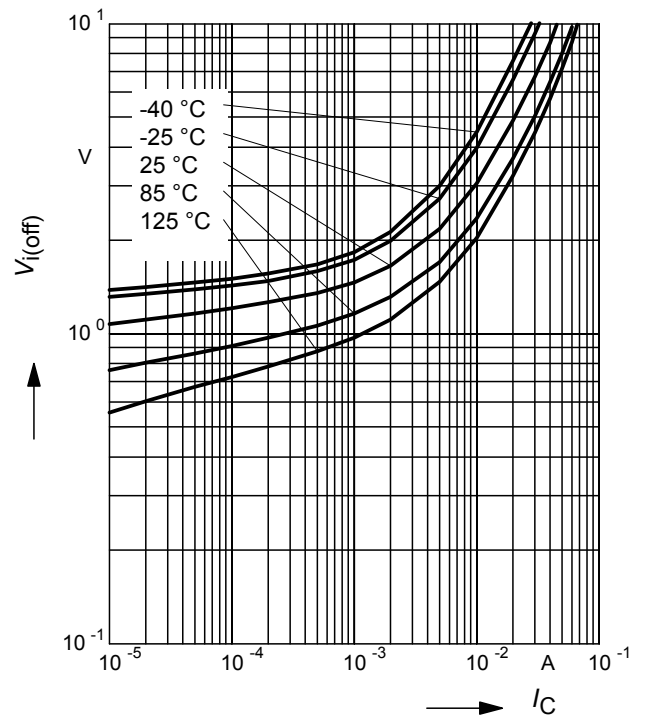
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$ (common emitter configuration)



Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



Total power dissipation $P_{tot} = f(T_S)$

BCR148



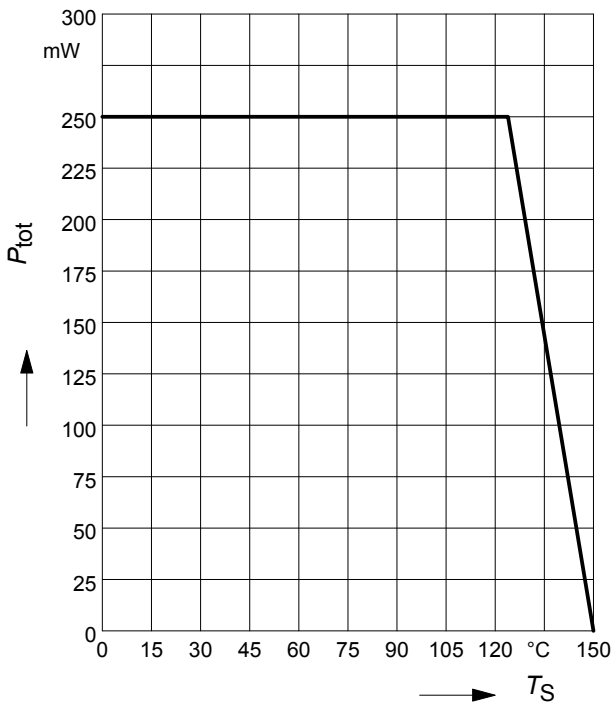
Total power dissipation $P_{tot} = f(T_S)$

BCR148S



Total power dissipation $P_{tot} = f(T_S)$

BCR148W



Permissible Pulse Load $R_{thJS} = f(t_p)$

BCR148



Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR148



Permissible Puls Load $R_{\text{thJS}} = f(t_p)$

BCR148S



Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR148S



Permissible Puls Load $R_{\text{thJS}} = f(t_p)$

BCR148W



Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR148W



Package Outline



Foot Print



Marking Layout (Example)

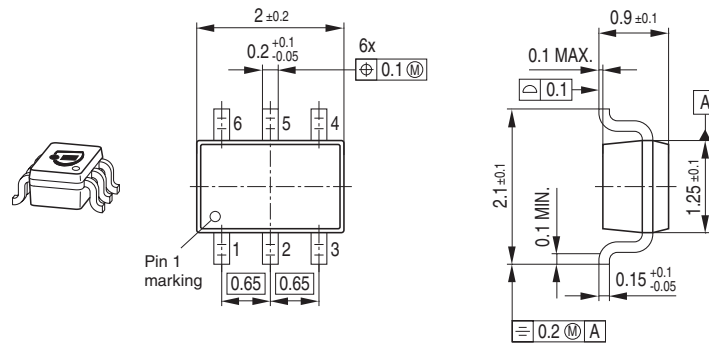


Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel



Package Outline

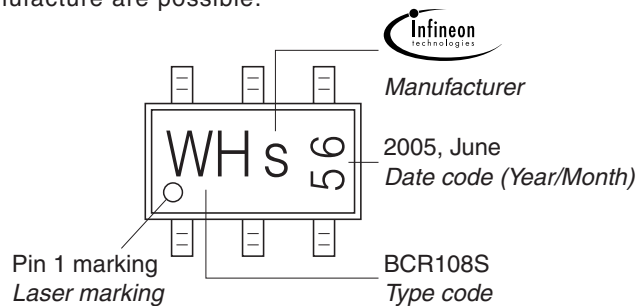


Foot Print



Marking Layout (Example)

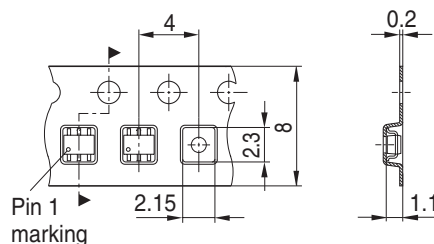
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel $\phi 180 \text{ mm} = 3.000 \text{ Pieces/Reel}$
 Reel $\phi 330 \text{ mm} = 10.000 \text{ Pieces/Reel}$

For symmetric types no defined Pin 1 orientation in reel.



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